

Please add new claims 52-59 as follows:

--52. (New) An in-process semiconductor structure, comprising:

a substrate;

a plurality of active regions;

a plurality of isolation regions adjacent the active regions, each isolation region being positioned between adjacent active regions to isolate adjacent active regions and no layers being formed on the isolation regions; and

at least one selectively formed contact region on each active region, each selectively formed contact region being isolated from contacts on adjacent active regions.

53. (New) The in-process semiconductor structure of claim 52 wherein each isolation region comprises a field oxide region.

54. (New) The in-process semiconductor of claim 53 wherein the substrate comprises silicon.

55. (New) The in-process semiconductor of claim 53 wherein the substrate comprises gallium arsenide.

56. (New) The in-process semiconductor of claim 53 wherein the substrate comprises silicon germanium.

57. (New) The in-process semiconductor of claim 53 wherein each contact comprises selective epitaxial growth silicon.

58. (New) The in-process semiconductor of claim 53 wherein at least some of the contacts comprise gallium arsenide.